

Study on the Influence of spatial distribution of nitrogen concentration on the uniformity of GaN crystal growth using Na-flux method

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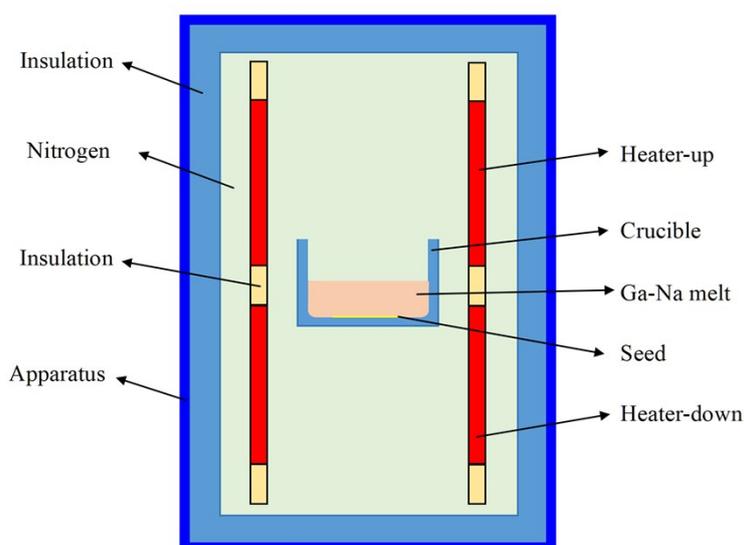


Fig.S1 Schematic diagram of the device for growing GaN by Na-flux method

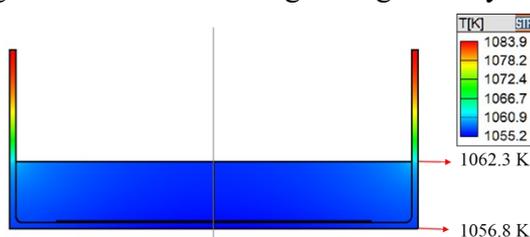


Fig.S2 Temperature distribution of crucible